

TOSHIBA Photocoupler GaAs Ired & Photo-Transistor

TLP330

Programmable Controllers

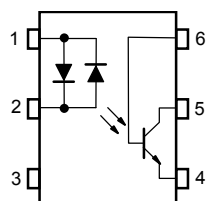
AC / DC-Input Module

Telecommunication

The TOSHIBA TLP330 consists of a photo-transistor optically coupled to two gallium arsenide infrared emitting diode connected inverse parallel in a six lead plastic DIP package. This is suitable for application of AC input current up to 150mA.

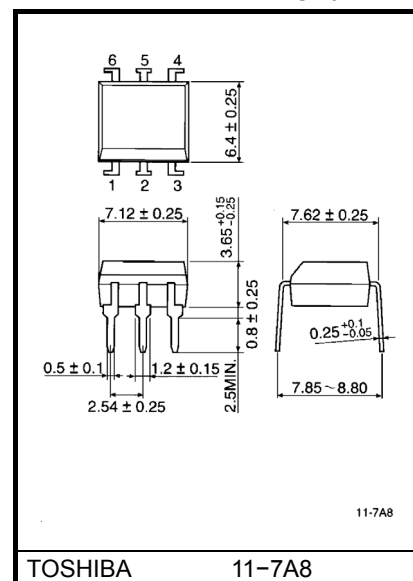
- If maximum rating: $\pm 150\text{mA}$
- Collector-Emitter voltage: $55\text{V}(\text{min.})$
- Current transfer ratio: $25\%(\text{min.})(I_F = \pm 20\text{mA})$
- Isolation voltage: $5000\text{Vrms}(\text{min.})$
- UL recognized: UL1577, file no. E67349

Pin Configurations (top view)



- 1: Anode, cathode
- 2: Cathode, anode
- 3: NC
- 4: Emitter
- 5: Collector
- 6: Base

Unit in mm



TOSHIBA 11-7A8

Weight: 0.39 g

Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit
LED	Forward current	I_F	± 150	mA
	Forward current derating (Ta $\geq 25^\circ\text{C}$)	$\Delta I_F / ^\circ\text{C}$	-1.5	mA / $^\circ\text{C}$
	Peak forward current (100 μs pulse, 100pps)	I_{FP}	± 1	A
	Junction temperature	T_j	125	$^\circ\text{C}$
Detector	Collector-emitter voltage	V_{CEO}	55	V
	Collector-base voltage	V_{CBO}	80	V
	Emitter-collector voltage	V_{ECO}	7	V
	Emitter-base voltage	V_{EBO}	7	V
	Collector current	I_C	80	mA
	Power dissipation	P_C	150	mW
	Power dissipation derating (Ta $\geq 25^\circ\text{C}$)	$\Delta P_C / ^\circ\text{C}$	-1.5	mW / $^\circ\text{C}$
	Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature range		T_{stg}	-55~125	$^\circ\text{C}$
Operating temperature range		T_{opr}	-55~100	$^\circ\text{C}$
Lead soldering temperature (10s)		T_{sol}	260	$^\circ\text{C}$
Total package power dissipation		P_T	250	mW
Total package power dissipation derating (Ta $\geq 25^\circ\text{C}$)		$\Delta P_T / ^\circ\text{C}$	-2.5	mW / $^\circ\text{C}$
Isolation voltage (AC, 1 min, R.H. $\leq 60\%$) (Note 1)		BV_S	5000	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

(Note 1) Device considered a two terminal device: Pins 1, 2 and 3 shorted together and pins 4, 5 and 6 shorted together.

Recommended Operating Conditions

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Supply voltage	V_{CC}	—	5	24	V
Forward current	$I_{F(RMS)}$	—	20	120	mA
Collector current	I_C	—	1	10	mA
Operating temperature	T_{opr}	-25	—	85	$^\circ\text{C}$

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

Individual Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Condition	Min.	Typ.	Max.	Unit
LED	Forward voltage	V_F	$I_F = \pm 100 \text{ mA}$	—	1.4	1.7	V
	Forward current	I_F	$V_F = \pm 0.7 \text{ V}$	—	2.5	20	μA
	Capacitance	C_T	$V = 0, f = 1 \text{ MHz}$	—	100	—	pF
Detector	Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 0.5 \text{ mA}$	55	—	—	V
	Emitter-collector breakdown voltage	$V_{(BR)ECO}$	$I_E = 0.1 \text{ mA}$	7	—	—	V
	Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 0.1 \text{ mA}$	80	—	—	V
	Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 0.1 \text{ mA}$	7	—	—	V
	Collector dark current	I_{CEO}	$V_{CE} = 24 \text{ V}$	—	10	100	nA
			$V_{CE} = 24 \text{ V}, T_a = 85^\circ\text{C}$	—	2	50	μA
	Collector dark current	I_{CER}	$V_{CE} = 24 \text{ V}, T_a = 85^\circ\text{C}$ $R_{BE} = 1 \text{ M}\Omega$	—	0.5	10	μA
	Collector dark current	I_{CBO}	$V_{CE} = 10 \text{ V}$	—	0.1	—	nA
	DC forward current gain	h_{FE}	$V_{CE} = 5 \text{ V}, I_C = 0.5 \text{ mA}$	—	400	—	—
	Capacitance (collector to emitter)	C_{CE}	$V = 0, f = 1 \text{ MHz}$	—	10	—	pF

Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Condition	Min.	Typ.	Max.	Unit
Current transfer ratio	I_C / I_F	$I_F = \pm 20 \text{ mA}, V_{CE} = 1 \text{ V}$	25	—	—	%
	$I_C / I_{F(\text{high})}$	$I_F = \pm 100 \text{ mA}, V_{CE} = 1 \text{ V}$	20	—	80	%
Base photo-current	I_{PB}	$I_F = \pm 5 \text{ mA}, V_{CB} = 5 \text{ V}$	—	10	—	μA
Collector-emitter saturation voltage	$V_{CE(\text{sat})}$	$I_C = 2.4 \text{ mA}, I_F = 20 \text{ mA}$	—	—	0.4	V
		$I_C = 2.4 \text{ mA}, I_F = \pm 100 \text{ mA}$	—	—	0.4	
Off-state collector current	$I_{C(\text{off})}$	$V_F = \pm 0.7 \text{ V}, V_{CE} = 24 \text{ V}$	—	1	10	μA
CTR symmetry	$I_C(\text{ratio})$	$I_C(I_F = -20 \text{ mA})$ $/ I_C(I_F = +20 \text{ mA})$	0.5	1	2	—

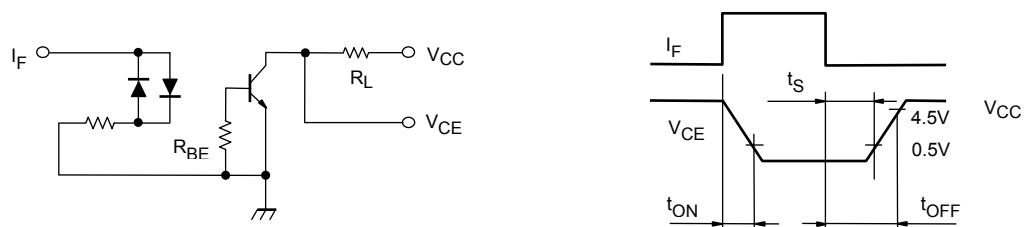
Isolation Characteristics (Ta = 25°C)

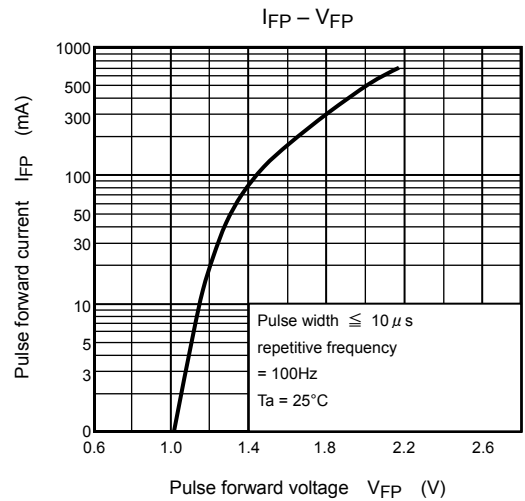
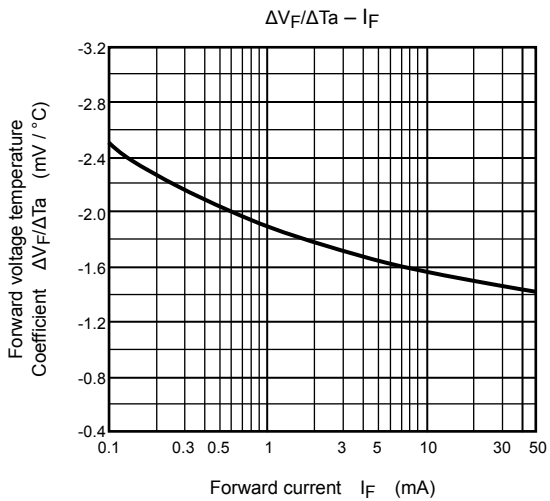
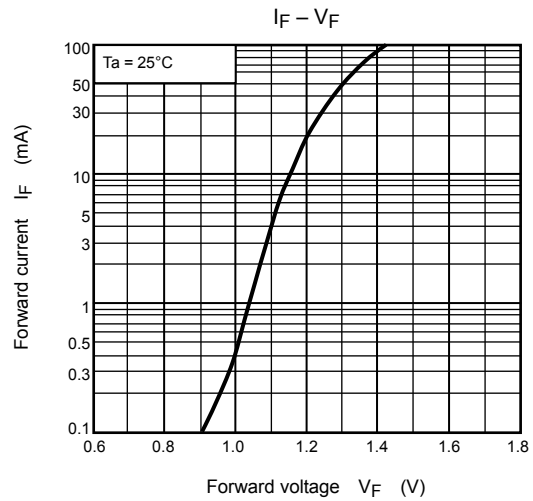
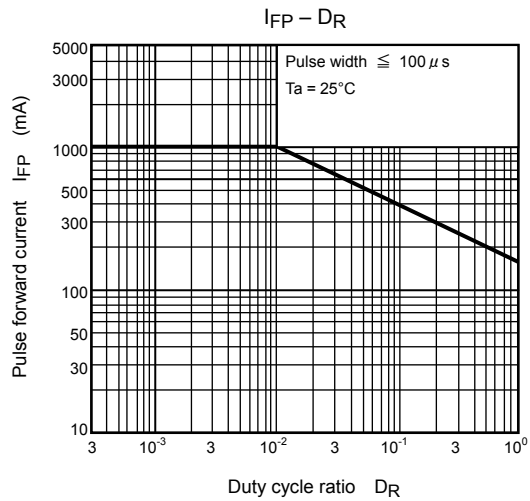
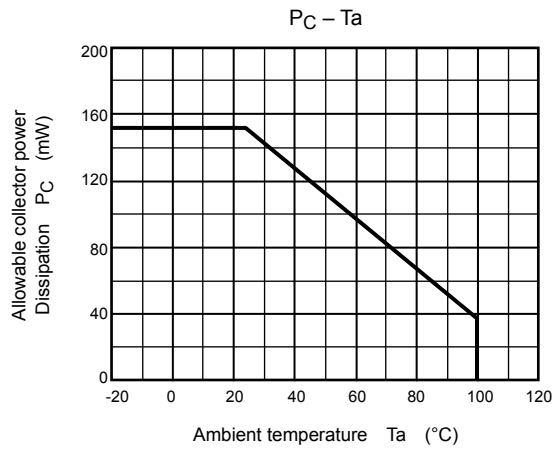
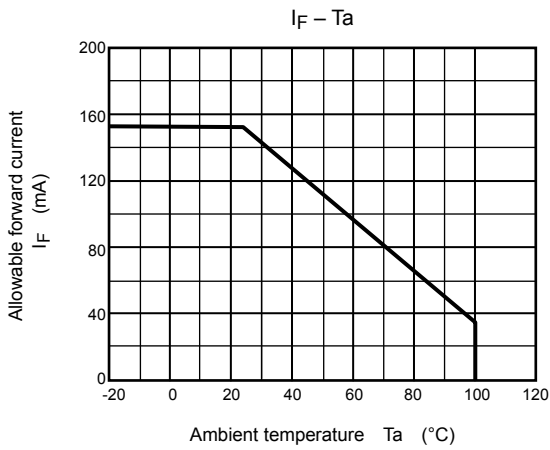
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Capacitance (input to output)	C _S	V _S = 0, f = 1 MHz	—	0.8	—	pF
Isolation resistance	R _S	V _S = 500 V, R.H. ≤ 60%	5×10 ¹⁰	10 ¹⁴	—	Ω
Isolation voltage	BV _S	AC, 1 minute	5000	—	—	Vrms
		AC, 1 second, in oil	—	10000	—	Vrms
		DC, 1 minute, in oil	—	10000	—	Vdc

Switching Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Rise time	t _r	V _{CC} = 10 V I _C = 2 mA R _L = 100Ω	—	2	—	μs
Fall time	t _f		—	3	—	
Turn-on time	t _{on}		—	3	—	
Turn-off time	t _{off}		—	3	—	
Turn-on time	t _{ON}	R _L = 1.9 kΩ (Fig.1) R _{BE} = OPEN V _{CC} = 5 V, I _F = ±16 mA	—	2	—	μs
Storage time	t _s		—	15	—	
Turn-off time	t _{OFF}		—	25	—	
Turn-on time	t _{ON}	R _L = 1.9 kΩ (Fig.1) R _{BE} = 220kΩ V _{CC} = 5 V, I _F = ±16 mA	—	2	—	μs
Storage time	t _s		—	12	—	
Turn-off time	t _{OFF}		—	20	—	

Fig. 1 Switching time test circuit





RESTRICTIONS ON PRODUCT USE

20070701-EN

- The information contained herein is subject to change without notice.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.
In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc.
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.
- The products described in this document shall not be used or embedded to any downstream products of which manufacture, use and/or sale are prohibited under any applicable laws and regulations.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any patents or other rights of TOSHIBA or the third parties.
- GaAs(Gallium Arsenide) is used in this product. The dust or vapor is harmful to the human body. Do not break, cut, crush or dissolve chemically.
- Please contact your sales representative for product-by-product details in this document regarding RoHS compatibility. Please use these products in this document in compliance with all applicable laws and regulations that regulate the inclusion or use of controlled substances. Toshiba assumes no liability for damage or losses occurring as a result of noncompliance with applicable laws and regulations.